

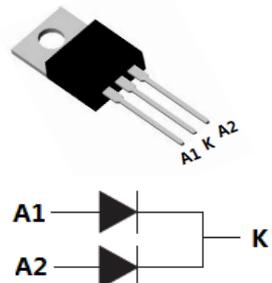
WSB20L100T

Power Schottky Barrier Rectifier

www.sh-willsemi.com

Features

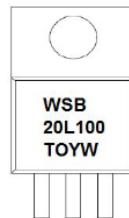
- 2x10A average rectified forward current
- Low forward voltage and Low leakage current
- High Junction temperature
- High forward and reverse Surge capability



Circuit

Applications

- High frequency switch model power supplies
- DC-DC Convertors, Power adapters



WSB20L100 = Device code
TO = Special code
Y = Year
W = Week (A~z)

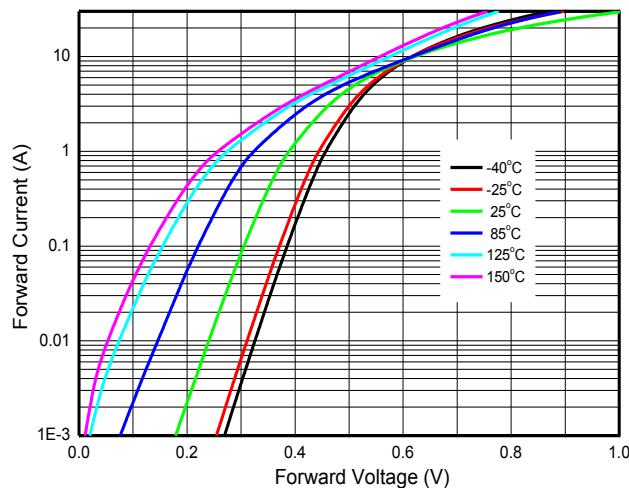
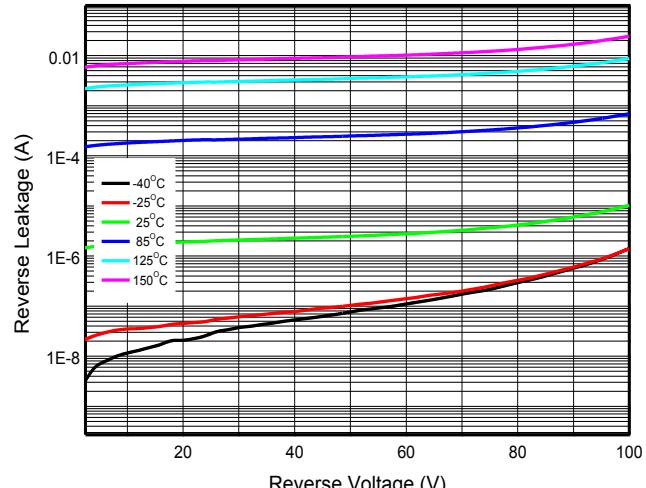
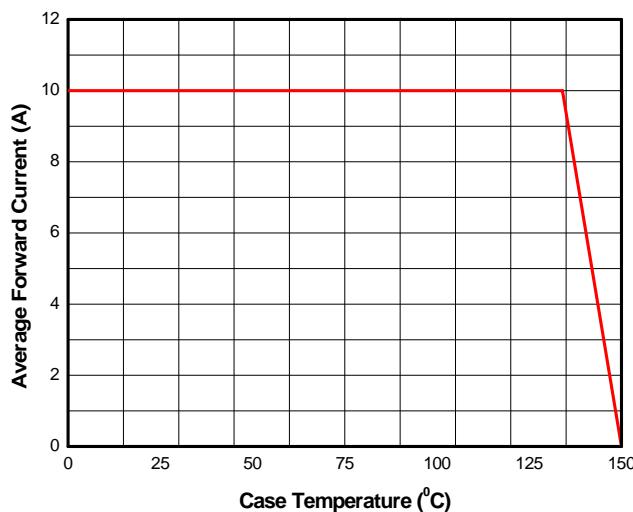
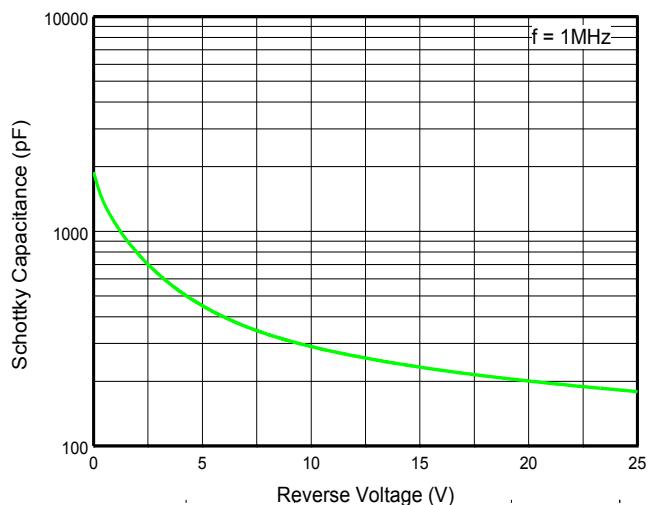
Marking

Absolute maximum ratings				
Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V _{RM}	100	V
Reverse voltage (DC)		V _R	100	V
Average rectified forward current	Per diode	I _F	10	A
	Per device	I _F	20	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave		I _{FSM}	200	A
Junction temperature		T _J	150	°C
Operating temperature		T _{opr}	-55 ~ 150	°C
Storage temperature		T _{stg}	-55 ~ 150	°C
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)	TO-220	R _{JC}	2.0	°C/W

Order information				
Device	Package	Marking	Units/Tube	
WSB20L100T-3/T	TO-220	WSB20L100TOYW	50	

Electronics characteristics (Per diode, $T_A = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_R	$I_R=0.5\text{mA}$	100			V
Forward voltage	V_F	$I_F=10\text{A}$		0.6	0.7	V
Reverse current	I_R	$V_R=100\text{V}$	-	11	100	μA
Junction capacitance	C_J	$V_R=25\text{V}, f=1\text{MHz}$	-	180		pF

Typical characteristics ($T_a=25^\circ\text{C}$, unless otherwise noted)

Forward voltage vs. Forward current

Reverse current vs. Reverse voltage

Forward Current Derating Curve

Junction capacitance vs. Reverse voltage

Package outline dimensions

TO-220

